

isc Silicon NPN Power Transistor

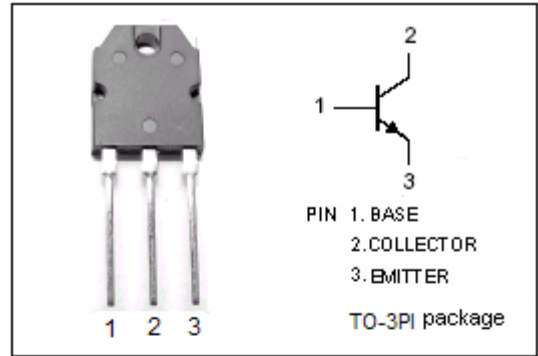
2SC3657

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 800V(\text{Min})$
- Fast Switching Speed

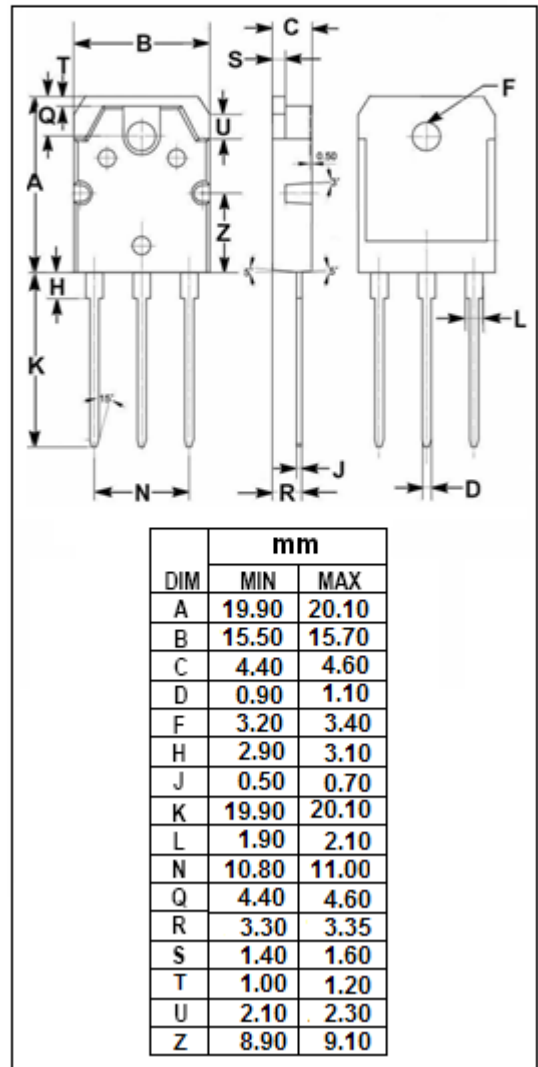
APPLICATIONS

- Switching regulator and high voltage switching applications
- High speed DC-DC converter applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	900	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-Peak	5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	80	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**2SC3657****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	900			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.4\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2\text{A}; I_B=0.4\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=800\text{V}; I_E=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			1	mA
h_{FE}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	10			

Switching times

t_r	Rise Time	$I_C=1\text{A}; I_{B1}=-I_{B2}=-0.4\text{A};$ $R_L=400\Omega; V_{CC}\approx 400\text{V}$			1.0	μs
t_{stg}	Storage Time				2.5	μs
t_f	Fall Time				1.0	μs

◆ **h_{FE-1} Classifications**

K	L	M
10-20	15-30	20-40